

Device Modeling Report

COMPONENTS:
DIODE/ GENERAL PURPOSE RECTIFIER / STANDARD
PART NUMBER: 1SR154-400
MANUFACTURER: ROHM
REMARK: TC=150C

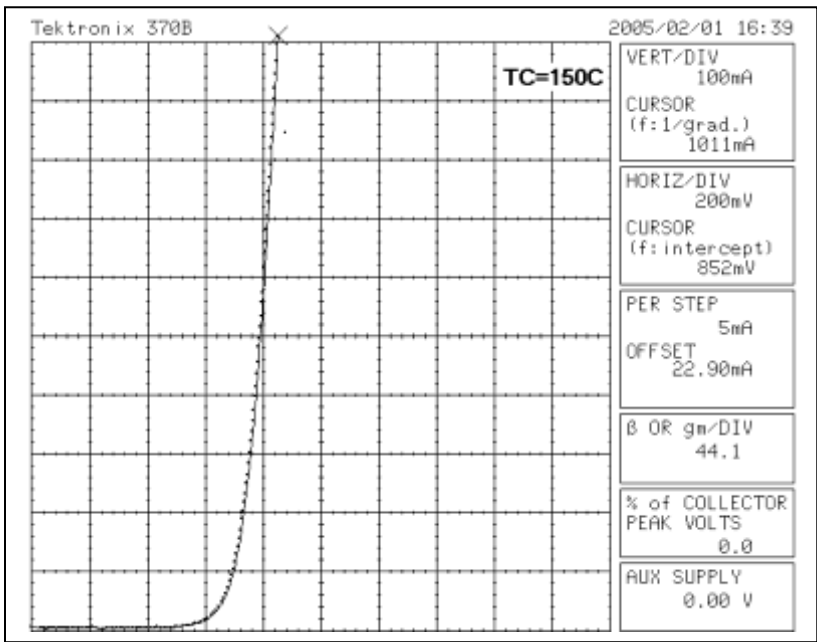


Bee Technologies Inc.

PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

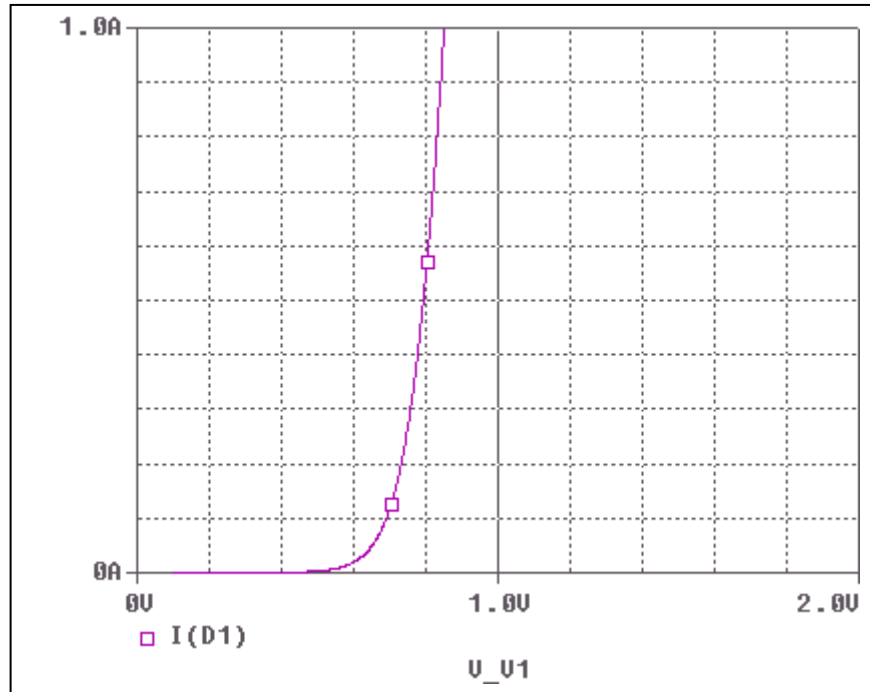
Forward Current Characteristic

Reference

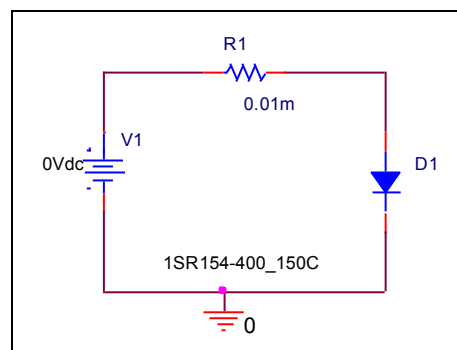


Forward Current Characteristic

Circuit Simulation Result

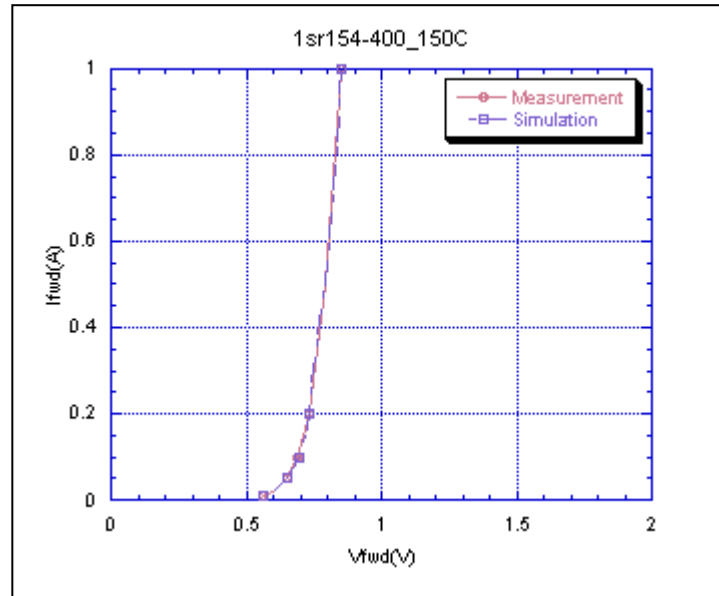


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

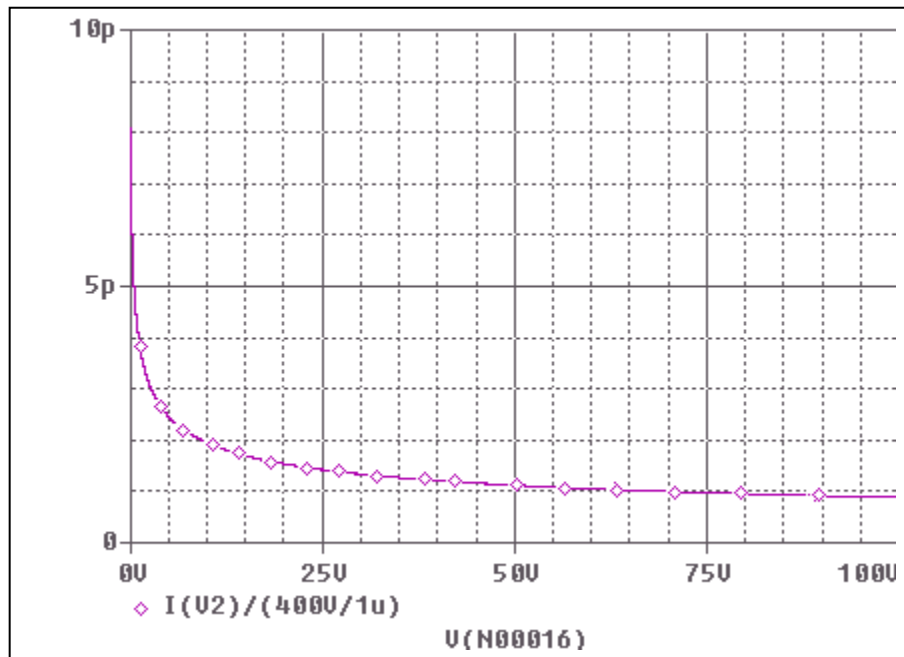


Simulation Result

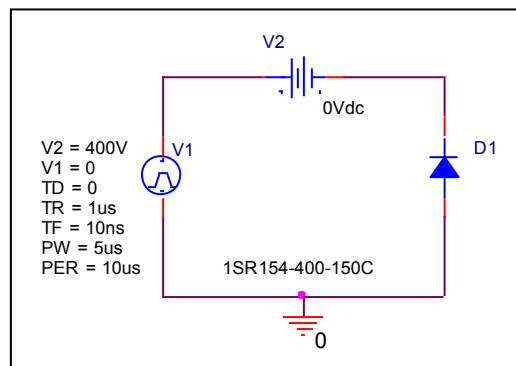
I_{fwd} (A)	V_{fwd} (V) Measurement	V_{fwd} (V) Simulation	%Error
0.01	0.565	0.563	0.35
0.02	0.600	0.601	-0.17
0.05	0.650	0.651	-0.15
0.1	0.692	0.693	-0.14
0.2	0.734	0.732	0.27
0.5	0.790	0.793	-0.38
1	0.852	0.851	0.12

Capacitance Characteristic

Circuit Simulation Result

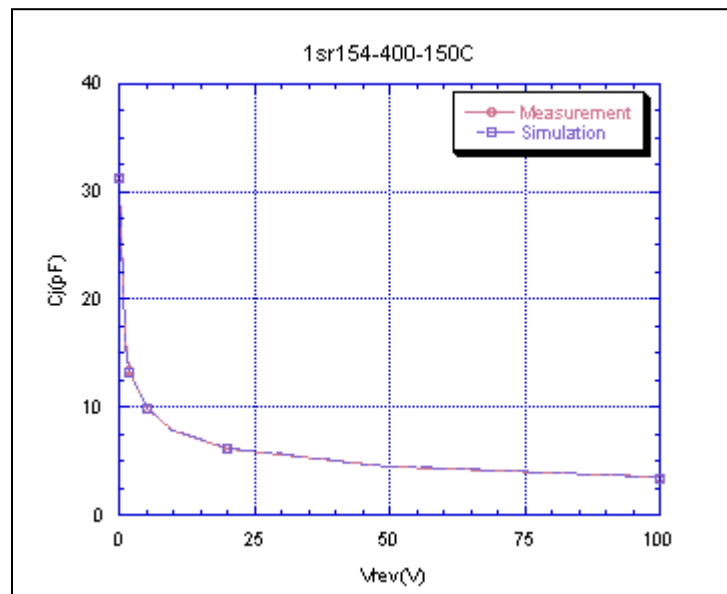


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

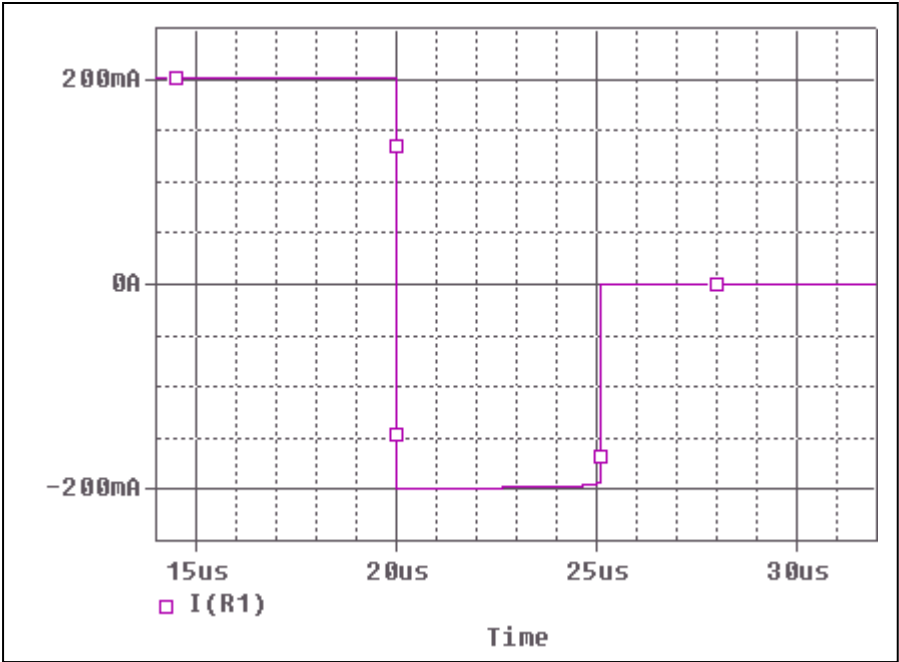


Simulation Result

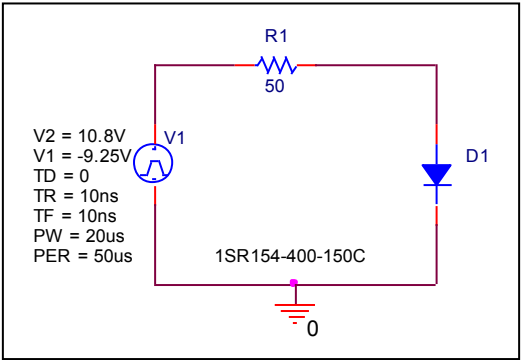
V_{rev} (V)	C_j (pF) Measurement	C_j (pF) Simulation	%Error
0	31.299	31.299	0.00
1	16.474	16.413	0.37
2	13.327	13.278	0.37
5	9.918	9.847	0.72
10	7.816	7.793	0.29
20	6.120	6.150	-0.49
50	4.409	4.486	-1.75
100	3.460	3.372	2.54

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

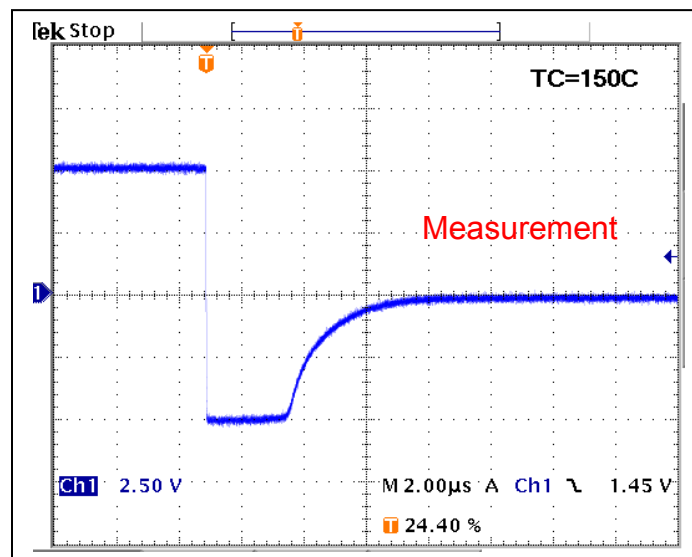


Compare Measurement vs. Simulation

	Measurement		Simulation		%Error
trr	5.08	us	5.08	us	0.00

Reverse Recovery Characteristic

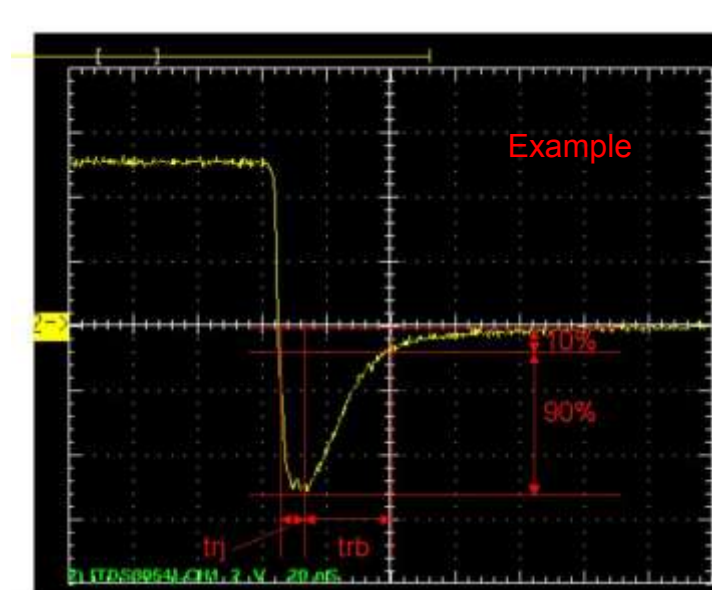
Reference



$T_{rr} = 2.64(\mu s)$

$T_{rb} = 2.44(\mu s)$

Conditions: $I_{fwd} = I_{rev} = 0.2(A)$, $R_L = 50$



Relation between t_{rr} and t_{rb}